

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	((split-gate adj flash adj memory adj cell) and (N-type adj well adj region) and (P+ adj source) and (P+ adj drain) and (channel adj region adj extending) and (first adj insulating adj layer) and (floating adj gate) and (control adj gate) and (programmed adj3 band-to-band) and (hot adj electron) and (technique adj erased) and (polysilicon-polysilicon adj tunneling adj technique)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 10:33
L2	63	chu-wen-ting.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 10:33
L3	151	hsieh-chia-ta.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 10:33
S1	0	(band adj to adj band) and flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 13:52
S2	2954	(band adj2 band) and flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:48
S3	1061	S2 and eras\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:49
S4	970	S3 and program\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:49
S5	1	S4 and (polysilicon adj tunneling)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:50

S6	859	S4 and tunneling	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:50
S7	757	S6 and (floating adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:50
S8	480	S7 and (channel adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:50
S9	455	S8 and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:51
S10	134	S9 and (split adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 13:20
S11	38	S10 and (over adj erase)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 13:59
S12	45	S2 and BBHE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 13:19
S13	82	S4 and 365/185.05	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 13:19
S14	17	S13 and (split adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 13:19
S15	0	(band adj to adj band) same (program\$4 or writ\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 13:53

S16	1986	(band adj2 band) same (program\$4 or writ\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 13:53
S17	291	(eras\$3 same (polysilicon near9 tunneling))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 13:55
S18	27	S16 and S17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:56
S19	27	S18 and flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 14:27
S20	1	S19 and (over adj erase)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 13:59
S21	8	"6639835"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 14:27
S22	2954	(band adj2 band) and flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:55
S23	1061	S22 and eras\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:55
S24	970	S23 and program\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:55
S25	82	S24 and 365/185.05	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:55

S26	5	"6282124"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 15:56
S27	5	"6282124"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:51
S28	8	"6639835"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:51
S29	2954	(band adj2 band) and flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:57
S30	1061	S29 and eras\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:57
S31	970	S30 and program\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:57
S32	82	S31 and 365/185.05	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:58
S33	20	S32 and split	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:58
S34	291	(eras\$3 same (polysilicon near9 tunneling))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:10
S35	106	S34 and split	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:10

S36	37	S35 and N-type	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:10
S37	7	S36 and P+	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:10
S38	2954	(band adj2 band) and flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:13
S39	1061	S38 and eras\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:13
S40	970	S39 and program\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:13
S41	859	S40 and tunneling	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:13
S42	757	S41 and (floating adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:13
S43	480	S42 and (channel adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:13
S44	455	S43 and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:13
S45	134	S44 and (split adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:13

S46	38	S45 and (over adj erase)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:14
S47	13	S46 and p+	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:14
S48	9	S47 and N-type	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:19
S49	140595	N-type	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:19
S50	141348	P-type	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:19
S51	30706	N-type adj3 region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:20
S52	4198	S51 and P+	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:20
S53	476	S51 and (P+ adj source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:20
S54	147	S53 and (P+ adj drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:20
S55	21	S54 and split	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 12:21

S56	30706	N-type adj3 region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 13:21
S57	476	S56 and (P+ adj source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 13:21
S58	147	S57 and (P+ adj drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 13:21
S59	21	S58 and split	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:16
S60	2	"20050190595"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:53
S61	13	"6229176"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:55
S62	17	"5130769"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:57
S63	32932	(floating adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:58
S64	6311	S63 and (electric adj field)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:58
S65	6041	S64 and (memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:58

S66	302	S65 and tip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:58
S67	246	S66 and flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:58
S68	50	S67 and nand	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:59
S69	105	S67 and band	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:59
S70	47	S69 and tunneling	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:59
S71	27	S70 and split	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:51
S72	0	S71 and (dual adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:52
S73	23	S71 and (high adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:52
S74	1	S73 and dual	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:52
S75	23	S71 and (high adj voltages)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:03



S76	27	"5706227"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:03
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10/788949

Inventor: CHU , WEN-TING, et al









Status: 30 - DOCKETED NEW CASE - READY FOR EXAMINATION

Title: SPLIT-GATE P-CHANNEL FLASH MEMORY CELL WITH PROGRAMMING BY BAND-TO-BAND HOT ELECTRON METHOD

Examiner: NGUYEN, NAM

GAU: 2824  
Classification: 365/185.100

All tab report (8 items, not sorted)

img	Status	Doc Code	Document Type	Date	Pages	Annotations
	7	TRNA	Transmittal letter	02/27/2004	2	
	7	SPEC	Specification	02/27/2004	13	
	7	CLM	Claims	02/27/2004	4	
	7	ABST	Abstract	02/27/2004	1	
	7	DRW	Drawings	02/27/2004	3	
	7	OATH	Oath or Declaration filed	02/27/2004	4	
	7	WFEE	Fee Worksheet (PTO-875)	02/27/2004	1	
	7	WFEE	Fee Worksheet (PTO-875)	02/27/2004	1	